Abstracts

Power GaAs MESFET with a High Drain-Source Breakdown Voltage

M. Fukuta, K. Suyama, H. Suzuki, Y. Nakayama and H. Ishikawa. "Power GaAs MESFET with a High Drain-Source Breakdown Voltage." 1976 Transactions on Microwave Theory and Techniques 24.6 (Jun. 1976 [T-MTT] (Special Issue on Microwave Field-Effect Transistors)): 312-317.

A power GaAs MESFET with a high drain-source breakdown voltage in excess of 17 V has been developed. A selective GaAs epitaxial process is introduced to form "inlaid" n+ source and drain regions that can provide a high drain-source breakdown voltage and a low ohmic-contact resistance. Typical characteristics of the MESFET composed of two-cell units are as follows.

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